

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI )  
Serial No. 09/619,477 )  
Filed: July 19, 2000 )  
For: CONTACT STRUCTURE AND )  
SEMICONDUCTOR DEVICE )

Art Unit: 2813  
Examiner: E. Kielin

CERTIFICATE OF MAILING

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**PRELIMINARY AMENDMENT**

Honorable Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated May 7, 2002 please amend the above-  
identified application as follows:

**IN THE SPECIFICATION:**

Please amend the specification as follows:

**On Page 27, Paragraph 2**

Thereafter, a resist mask having a predetermined pattern is formed by using a photomask PM5 (Fig. 6A). Contact holes reaching the source or drain regions of the respective island-like semiconductor films are formed in the insulating films 138 and 139. Further, insulating films 138 and 139 are removed from the terminal section 182. The contact holes are formed by dry etching. In this case, a mixed gas of CF<sub>4</sub>, O<sub>2</sub> and He is used as the etching gas. The interlayer insulating film 139 formed of the organic resin material is first etched. Then, the etching gas is switched to CF<sub>4</sub> and O<sub>2</sub>, and the protective insulating film 138 is etched. To improve the selection ratio with the island-like semiconductor films, the etching gas is switched further to CHF<sub>3</sub> and the gate insulating film is etched. In this way, the contact holes can be formed satisfactorily.